*Opti**MOS**™*3 Power-Transistor
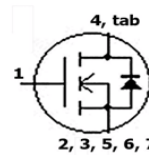
Features

• N-channel, normal level

• Excellent gate charge x $R_{DS(on)}$ product (FOM)

• Very low on-resistance $R_{DS(on)}$

• High current capability

• 175 °C operating temperature

• Pb-free lead plating; RoHS compliant

• Qualified according to JEDEC[1] for target application

• Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}	100	V
$R_{DS(on),max}$	3.9	mΩ
I_D	160	A

Type	IPB039N10N3 G
Package	PG-TO263-7
Marking	039N10N

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C[2]	160	A
		T_C=100 °C	113	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25 °C	640	
Avalanche energy, single pulse	E_{AS}	I_D=100 A, R_{GS}=25 Ω	340	mJ
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	214	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

[1] J-STD20 and JESD22

[2] See figure 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}		-	-	0.7	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3]	-	-	40	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=160 µA	2	2.7	3.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C	-	0.1	1	µA
		V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=100 A	-	3.3	3.9	mΩ
		V_{GS}=6 V, I_D=50 A	-	4.1	7.1	
Gate resistance	R_G		-	1.4	-	Ω
Transconductance	g_{fs}	$|V_{DS}|$>2$|I_D|R_{DS(on)max}$, I_D=100 A	76	152	-	S

[3] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz	-	6320	8410	pF
Output capacitance	C_{oss}		-	1210	1610	
Reverse transfer capacitance	C_{rss}		-	41	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=50 V, V_{GS}=10 V, I_{D}=100 A, R_{G}=1.6 Ω	-	27	-	ns
Rise time	t_{r}		-	59	-	
Turn-off delay time	$t_{d(off)}$		-	48	-	
Fall time	t_{f}		-	14	-	

Gate Charge Characteristics[4]

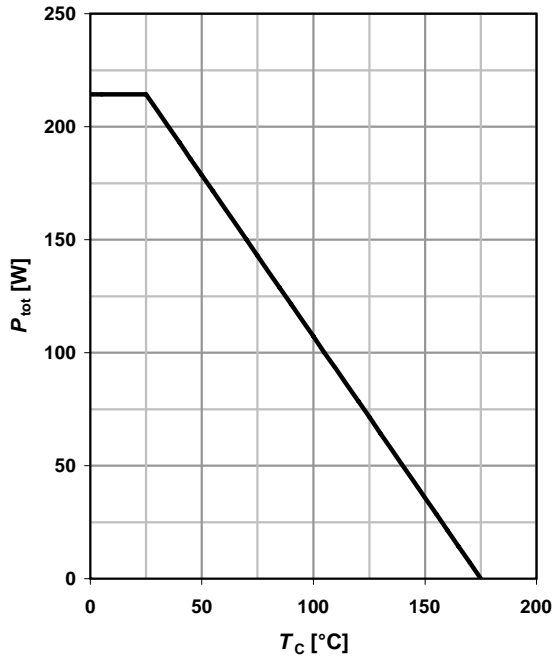| Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Gate to source charge	Q_{gs}	V_{DD}=50 V, I_{D}=100 A, V_{GS}=0 to 10 V	-	29	39	nC
Gate to drain charge	Q_{gd}		-	16	-	
Switching charge	Q_{sw}		-	26	-	
Gate charge total	Q_{g}		-	88	117	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	V
Output charge	Q_{oss}	V_{DD}=50 V, V_{GS}=0 V	-	122	162	nC

Reverse Diode

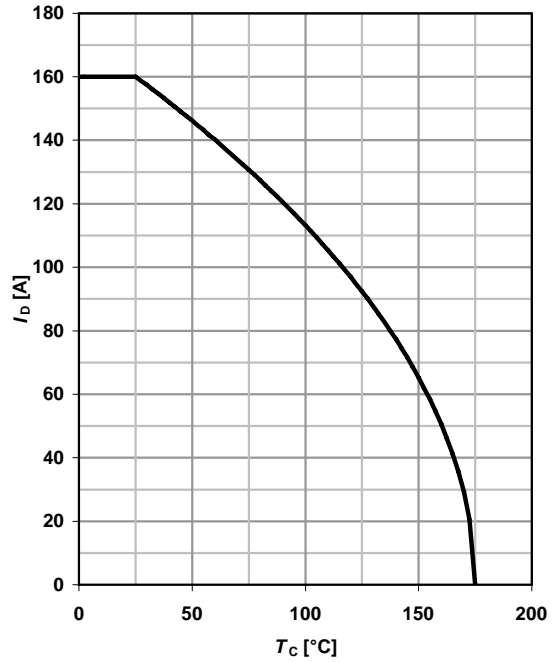| Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode continous forward current	I_{S}	T_{C}=25 °C	-	-	160	A
Diode pulse current	$I_{S,pulse}$		-	-	640	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_{F}=100 A, T_{j}=25 °C	-	1	1.2	V
Reverse recovery time	t_{rr}	V_{R}=50 V, I_{F}=100A, di_{F}/dt=100 A/µs	-	68	-	ns
Reverse recovery charge	Q_{rr}		-	135	-	nC

[4] See figure 16 for gate charge parameter definition
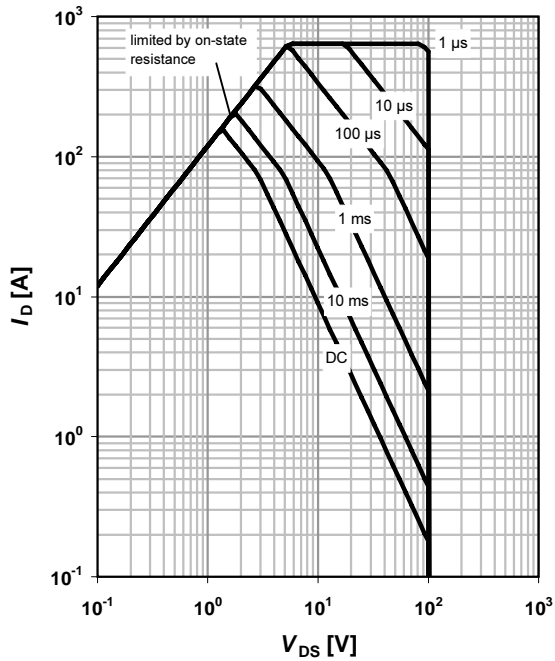
1 Power dissipation

P_{tot}=f(T_C)

2 Drain current

I_D=f(T_C); V_{GS}≥10 V

3 Safe operating area
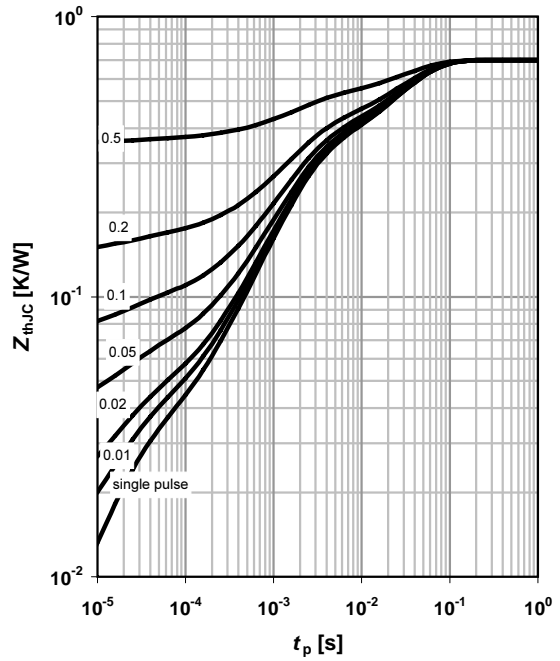
I_D=f(V_{DS}); T_C=25 °C; D=0

parameter: t_p

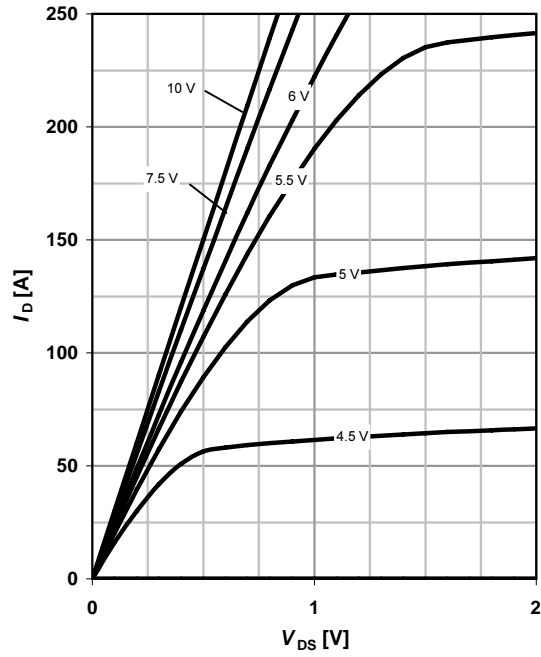**4 Max. transient thermal impedance**

Z_{thJC}=f(t_p)

parameter: D=t_p/T

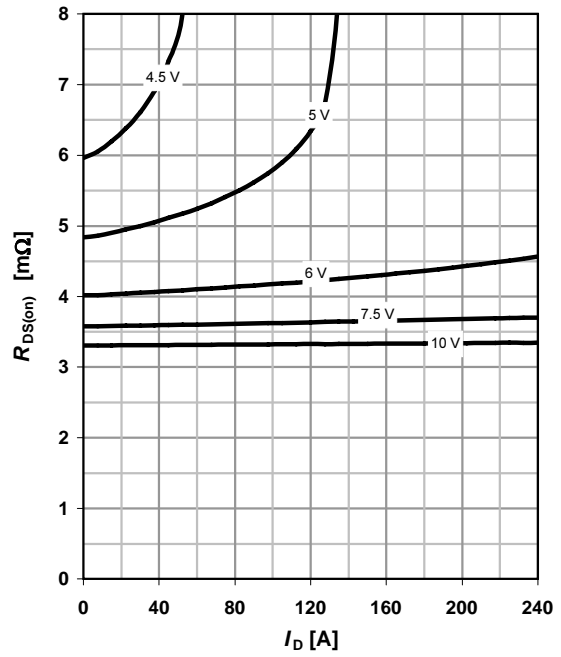**5 Typ. output characteristics**

I_D=f(V_{DS}); T_j=25 °C

parameter: V_{GS}

6 Typ. drain-source on resistance

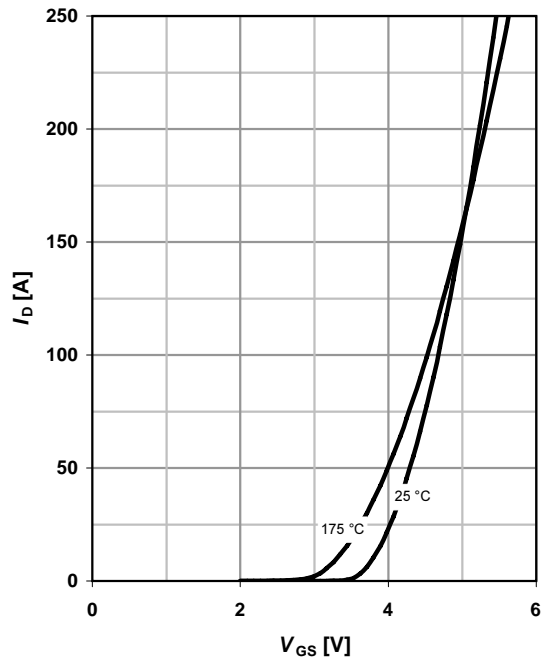$R_{DS(on)}$=f(I_D); T_j=25 °C

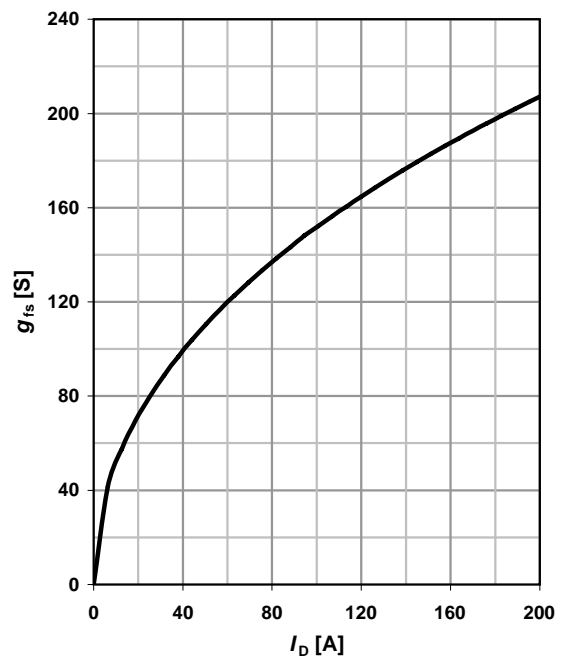parameter: V_{GS}

7 Typ. transfer characteristics

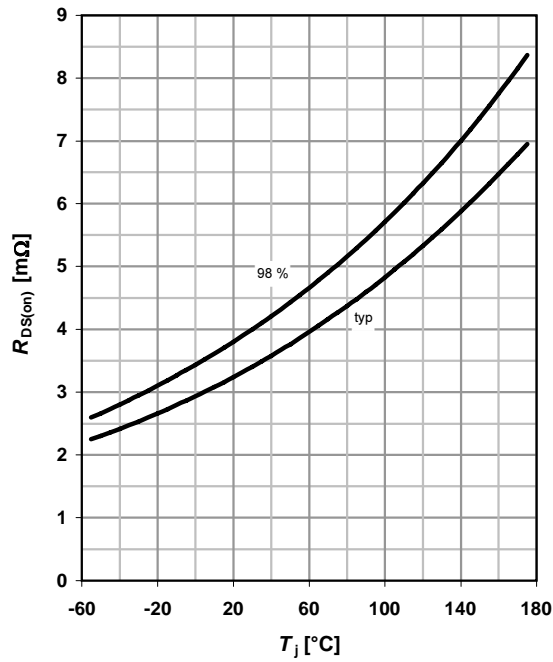I_D=f(V_{GS}); $|V_{DS}|$>2$|I_D|R_{DS(on)max}$

parameter: T_j

8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C
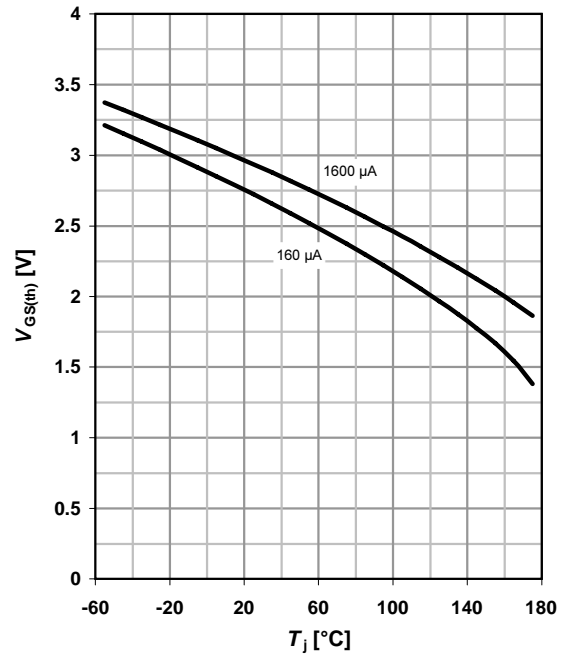
9 Drain-source on-state resistance

$R_{DS(on)}$=f(T_j); I_D=100 A; V_{GS}=10 V

10 Typ. gate threshold voltage

$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}

parameter: I_D

11 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

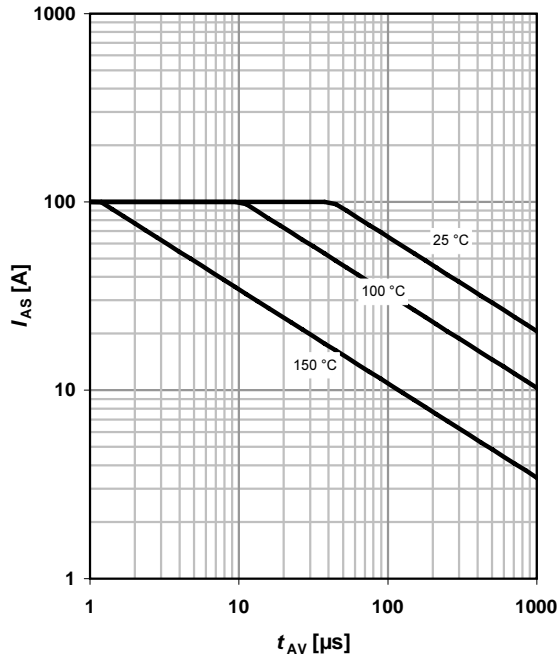**12 Forward characteristics of reverse diode**

I_F=f(V_{SD})

parameter: T_j

13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω
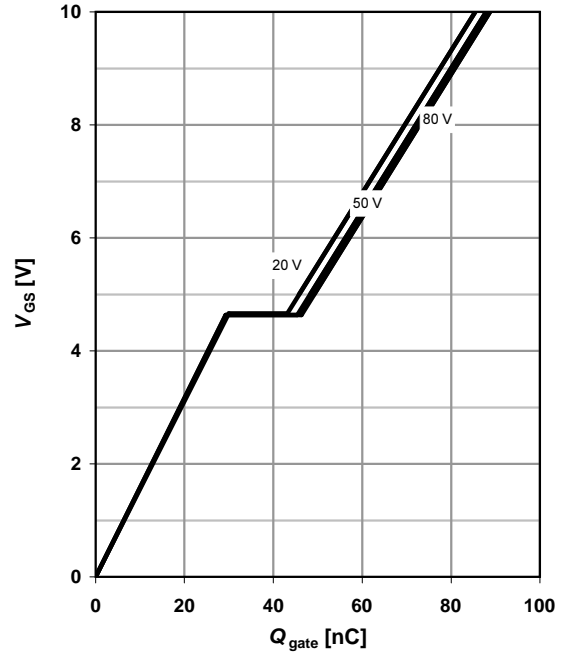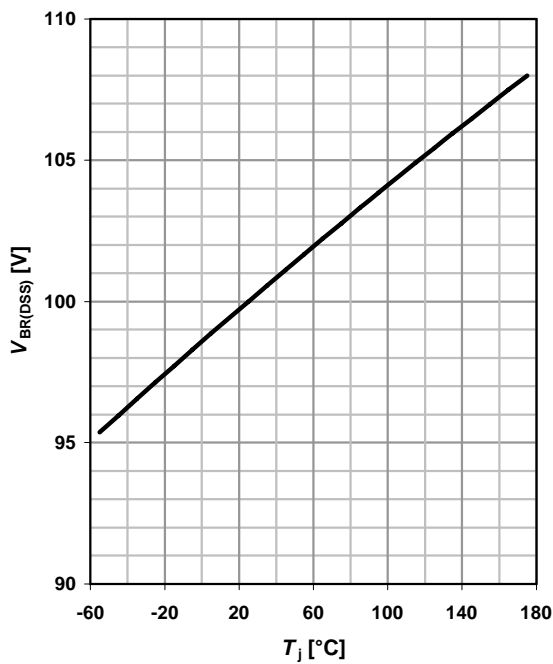
parameter: $T_{j(start)}$

14 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=100 A pulsed

parameter: V_{DD}

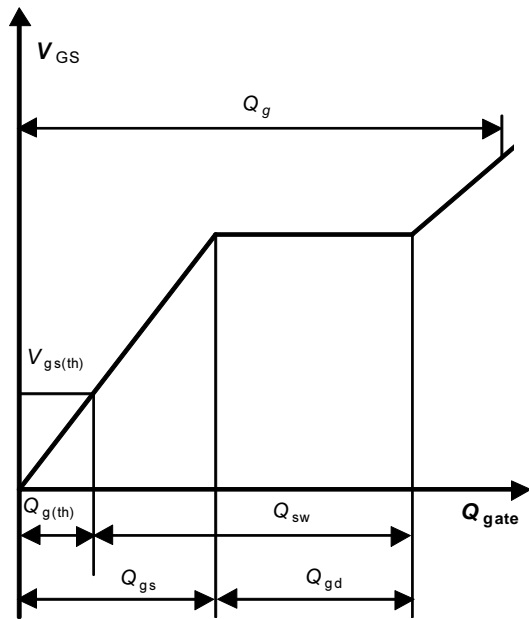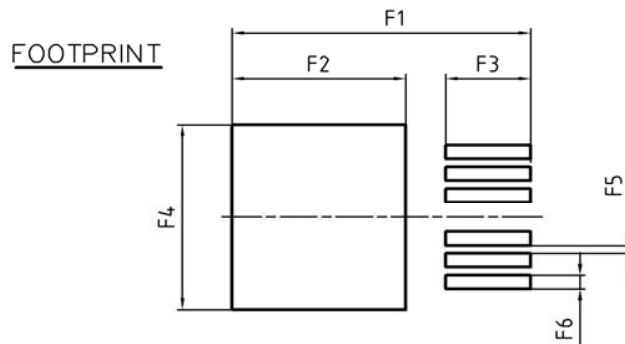**15 Drain-source breakdown voltage**

$V_{BR(DSS)}$=f(T_j); I_D=1 mA

16 Gate charge waveforms

PG-TO263-3: Outline

FOOTPRINT

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.50	0.70	0.020	0.028
b2	0.50	1.00	0.020	0.039
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	6.90	7.90	0.272	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	1.27		0.050	
N	6		6	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	0.37	0.57	0.015	0.022
F6	0.70	0.90	0.028	0.035

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SCALE 7.5mm

EUROPEAN PROJECTION

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REVISION 01

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